## Features:

- Infrared LED emitter
- Silicon phototransistor sensor
- Snap-in mounting
- Variable sensing distance over 36 " ( 91.4 cm )
- Low profile package
- 24 " $(61.0 \mathrm{~cm}$ ) wire leads


## Description:

The OPB100Z series consists of an infrared LED (OPB100-EZ) and phototransistor (OPB100-SZ) in separate plastic housings. The low cost, snap-in design requires no screws or other mounting hardware for ease of installation.

The emitter and sensor are not apertured, which allows separation distances in excess of 36 " ( 91.4 cm ) without concern for precise alignment. The front side clip allows mounting of the product to any 0.059 " ( 1.50 mm ) thick material.
This product is designed for general switching and low-speed data communications applications.

## Applications:

- Non-contact reflective object
- Non-contact interruptive sensing
- Assembly line automation
- Machine automation
- Machine safety

| Ordering Information |  |  |  |
| :---: | :---: | :---: | :---: |
| Part <br> Number | LED Peak <br> Wavelength | Sensor | Lead Length / <br> Spacing |
| OPB100-EZ | 880 nm |  | 24" / 26 AWG |
| OPB100-SZ |  | Transistor | Wire |
| OPB100Z | Contains both OPB100-EZ \& OPB100-SZ |  |  |



## Optical Emitter and Sensor Pair OPB100Z, OPB100-EZ, OPB100-SZ

Absolute Maximum Ratings ( $\mathrm{T}_{\mathrm{A}}=25^{\circ} \mathrm{C}$ unless otherwise noted)

| Storage Temperature Range | $-40^{\circ} \mathrm{C}$ to $+85^{\circ} \mathrm{C}$ |
| :--- | :--- |
| Operating Temperature Range ${ }^{(1)}$ | $-40^{\circ} \mathrm{C}$ to $+80^{\circ} \mathrm{C}$ |

Input LED (OP298 for additional information)

| Forward DC Current | 100 mA |
| :--- | :---: |
| Peak Forward Current $(1 \mu$ s pulse width, 300 pps$)$ | 1 A |
| Reverse DC Voltage | 2 V |
| Power Dissipation $^{(2)}$ | 142 mW |

Output Phototransistor (OP598 for additional information)

| Collector-Emitter Voltage | 30 V |
| :--- | :---: |
| Emitter-Collector Voltage | 5 V |
| Collector DC Current | 50 mA |
| Power Dissipation $^{(3)}$ | 250 mW |

Electrical Characteristics ( $\mathrm{T}_{\mathrm{A}}=25^{\circ} \mathrm{C}$ unless otherwise noted - for reference only)

| SYMBOL | PARAMETER | MIN | TYP | MAX | UNITS | TEST CONDITIONS |
| :--- | :---: | :---: | :---: | :---: | :---: | :---: |

Input Diode (See OP298 for additional information - for reference only)

| $\mathrm{V}_{\mathrm{F}}$ | Forward Voltage | - | - | 1.7 | V | $\mathrm{I}_{\mathrm{F}}=20 \mathrm{~mA}$ |
| :---: | :--- | :---: | :---: | :---: | :---: | :--- |
| $\mathrm{I}_{\mathrm{R}}$ | Reverse Current | - | - | 15 | $\mu \mathrm{~A}$ | $\mathrm{~V}_{\mathrm{R}}=10 \mathrm{~V}$ |
| $\mathrm{q}_{\mathrm{HP}}$ | Emission Angle at Half Power Points | - | 25 | - | Degree | $\mathrm{I}_{\mathrm{F}}=20 \mathrm{~mA}$ |
| $\mathrm{E}_{\mathrm{E}}(\mathrm{APT})$ | Apertured Radiant Intensity | 6.5 | - | - | $\mathrm{mW} / \mathrm{cm}^{2}$ | $\mathrm{I}_{\mathrm{F}}=100 \mathrm{~mA}$ <br> Distance $=1.43 "(3.63 \mathrm{~cm})$ <br> Aperture $=0.25 "(6.35 \mathrm{~mm})$ |

Output Phototransistor (See OP598 for additional information - for reference only)

| $\mathrm{V}_{\text {(BR)CEO }}$ | Collector-Emitter Breakdown Voltage | 30 | - | - | V | $\mathrm{I}_{\mathrm{C}}=1 \mathrm{~mA}, \mathrm{E}_{\mathrm{E}}=0 \mathrm{mw} / \mathrm{cm}^{2}$ (no light) |
| :---: | :--- | :---: | :---: | :---: | :---: | :---: |
| $\mathrm{V}_{\text {(BR)ECO }}$ | Emitter-Collector Breakdown Voltage | 5 | - | - | V | $\mathrm{I}_{\mathrm{C}}=100 \mu \mathrm{~A}, \mathrm{E}_{\mathrm{E}}=0 \mathrm{mw} / \mathrm{cm}^{2}$ (no light) |
| $\mathrm{I}_{\mathrm{CEO}}$ | Collector Dark Current | - | - | 100 | nA | $\mathrm{V}_{\mathrm{CE}}=10 \mathrm{~V}, \mathrm{I}_{\mathrm{F}}=0, \mathrm{E}_{\mathrm{E}}=0 \mathrm{mw} / \mathrm{cm}^{2}$ <br> $(\mathrm{no}$ <br> light) |
| $\mathrm{V}_{\mathrm{CE}(\mathrm{SAT})}$ | Collector-Emitter Saturation Voltage | - | - | 0.4 | V | $\mathrm{I}_{\mathrm{C}}=400 \mu \mathrm{~A}, \mathrm{E}_{\mathrm{E}}=1.7 \mathrm{mw} / \mathrm{cm}^{2}$ |
| $\mathrm{I}_{\mathrm{C}(\mathrm{ON})}$ | On-State Collector Current | 5 | - | - | mA | $\mathrm{V}_{\mathrm{CE}}=5 \mathrm{~V}, \mathrm{E}_{\mathrm{E}}=1.7 \mathrm{mw} / \mathrm{cm}^{2}$ |

Notes:

1. Derate linearly $3.33 \mathrm{~mW} /{ }^{\circ} \mathrm{C}$ above $25^{\circ} \mathrm{C}$.
2. All parameters measured using pulse technique.
3. Derate linearly $1.43 \mathrm{~mW} /{ }^{\circ} \mathrm{C}$ above $25^{\circ} \mathrm{C}$.

Output Current vs. Distance


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